

EFFECT OF UNIAXIAL PRESSURE
ON THE COEFFICIENT OF FREE
CARRIER OPTICAL ABSORPTION
IN MANY-VALLEY SEMICONDUCTORS (*n*-Ge)

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S u m m a r y

The effect of a uniaxial elastic deformation on the polarization dependence of the coefficient of free carrier optical absorption is considered with regard for the carrier scattering by acoustic phonons and impurity atoms. The optical absorption coefficient for *n*-Ge is numerically calculated both in the quantum and in the classical frequency range.